

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (U-MOSIII)

SSM6N24TU

High Speed Switching Applications

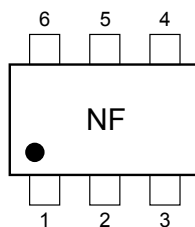
- Optimum for high-density mounting in small packages
- Low on-resistance: $R_{on} = 145m\Omega$ (max) (@ $V_{GS} = 4.5$ V)
 $R_{on} = 180m\Omega$ (max) (@ $V_{GS} = 2.5$ V)

Maximum Ratings (Ta = 25°C)

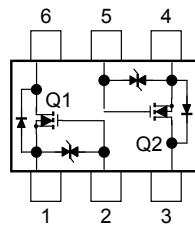
Characteristics		Symbol	Rating	Unit
Drain-Source voltage		V_{DS}	30	V
Gate-Source voltage		V_{GSS}	± 12	V
Drain current	DC	I_D	0.5	A
	Pulse	I_{DP}	1.5	
Drain power dissipation		P_D (Note1)	500	mW
Channel temperature		T_{ch}	150	°C
Storage temperature range		T_{stg}	-55~150	°C

Note1: Mounted on FR4 board. (total dissipation)
(25.4 mm × 25.4 mm × 1.6 t, Cu Pad: 645 mm²)

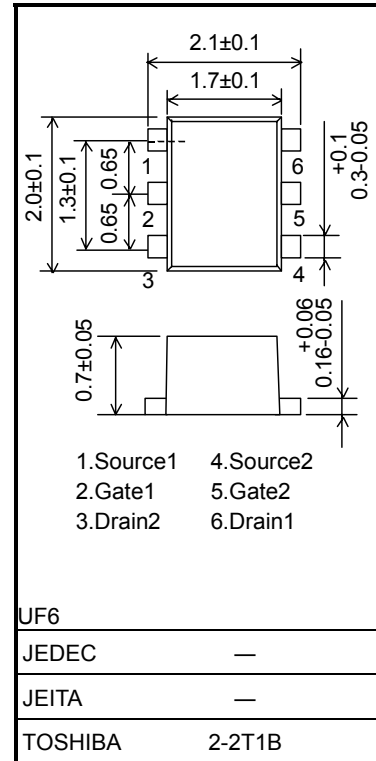
Marking



Equivalent Circuit (top view)



Unit: mm



Weight: 7.0 mg (typ.)

Handling Precaution

When handling individual devices (which are not yet mounted on a circuit board), be sure that the environment is protected against electrostatic electricity. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.

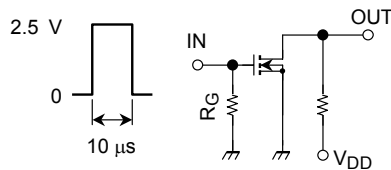
Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current	I_{GSS}	$V_{GS} = \pm 12\text{ V}, V_{DS} = 0$	—	—	± 1	μA
Drain-Source breakdown voltage	$V_{(BR)DSS}$	$I_D = 1\text{ mA}, V_{GS} = 0$	30	—	—	V
	$V_{(BR)DSX}$	$I_D = 1\text{ mA}, V_{GS} = -12\text{ V}$	18	—	—	
Drain cut-off current	I_{DSS}	$V_{DS} = 30\text{ V}, V_{GS} = 0$	—	—	1	μA
Gate threshold voltage	V_{th}	$V_{DS} = 3\text{ V}, I_D = 0.1\text{ mA}$	0.5	—	1.1	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 3\text{ V}, I_D = 0.25\text{ A}$ (Note2)	1.0	2.0	—	S
Drain-Source on-resistance	$R_{DS(ON)}$	$I_D = 0.50\text{ A}, V_{GS} = 4.5\text{ V}$ (Note2)	—	120	145	$\text{m}\Omega$
		$I_D = 0.25\text{ A}, V_{GS} = 2.5\text{ V}$ (Note2)	—	140	180	
Input capacitance	C_{iss}	$V_{DS} = 10\text{ V}, V_{GS} = 0, f = 1\text{ MHz}$	—	245	—	pF
Reverse transfer capacitance	C_{rss}	$V_{DS} = 10\text{ V}, V_{GS} = 0, f = 1\text{ MHz}$	—	33	—	pF
Output capacitance	C_{oss}	$V_{DS} = 10\text{ V}, V_{GS} = 0, f = 1\text{ MHz}$	—	41	—	pF
Switching time	Turn-on time	$V_{DD} = 10\text{ V}, I_D = 0.25\text{ A},$ $V_{GS} = 0 \sim 2.5\text{ V}, R_G = 4.7\text{ }\Omega$	—	9	—	ns
	Turn-off time		—	15	—	

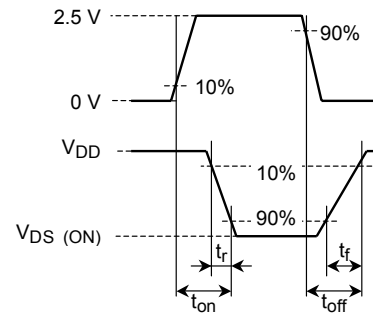
Note2: Pulse test

Switching Time Test Circuit

(a) Test Circuit



$V_{DD} = 10\text{ V}$
 $R_G = 4.7\text{ }\Omega$
 $\text{D.U.} \leq 1\%$
 $V_{IN}: t_r, t_f < 5\text{ ns}$
 Common Source
 $T_a = 25^\circ\text{C}$

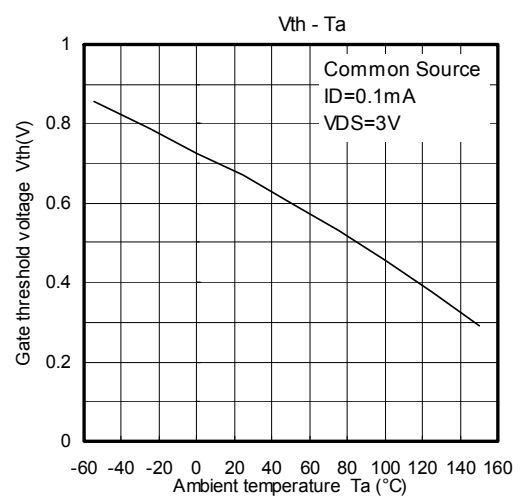
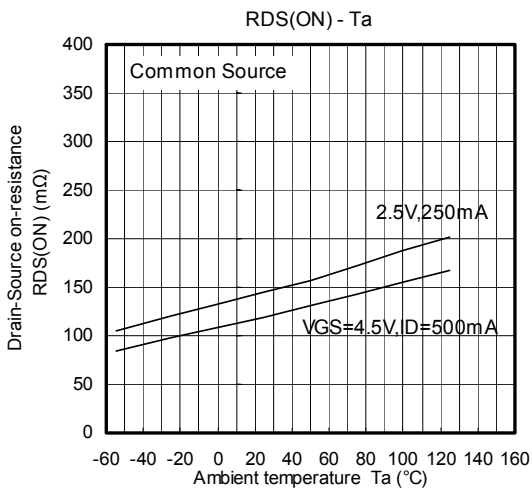
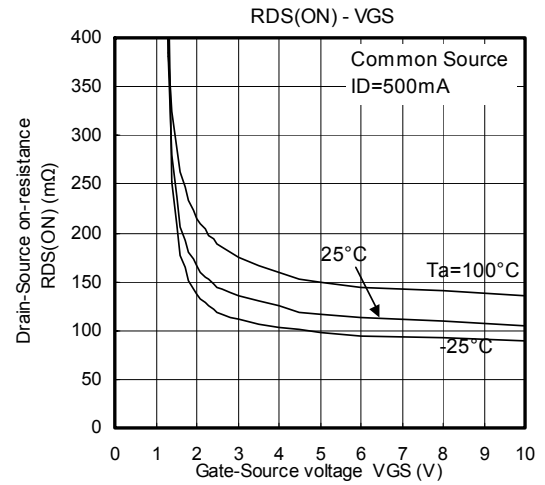
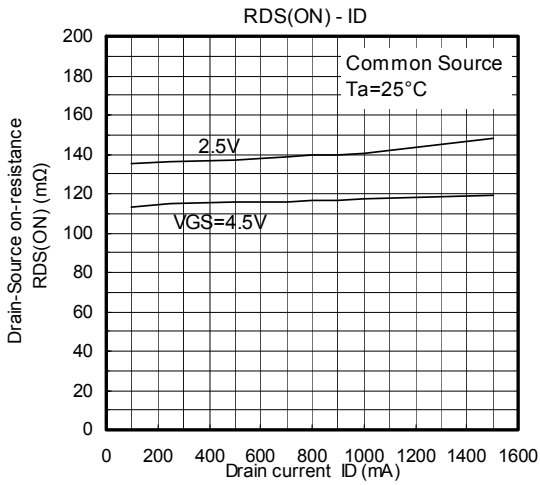
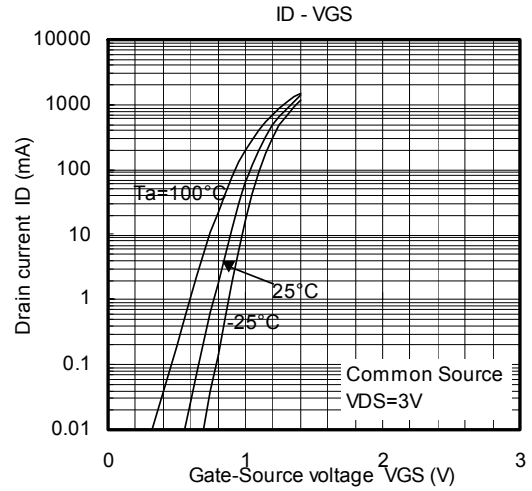
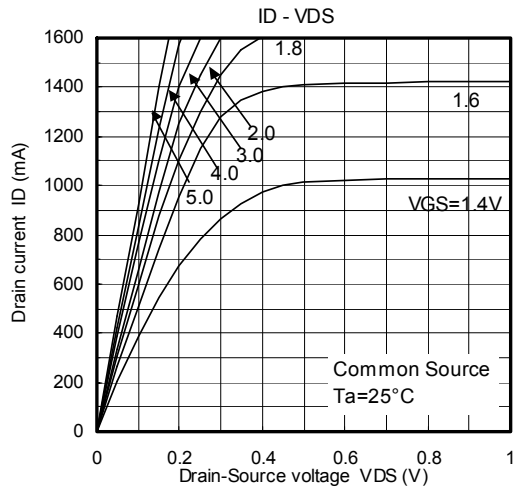
(b) V_{IN} (c) V_{OUT}

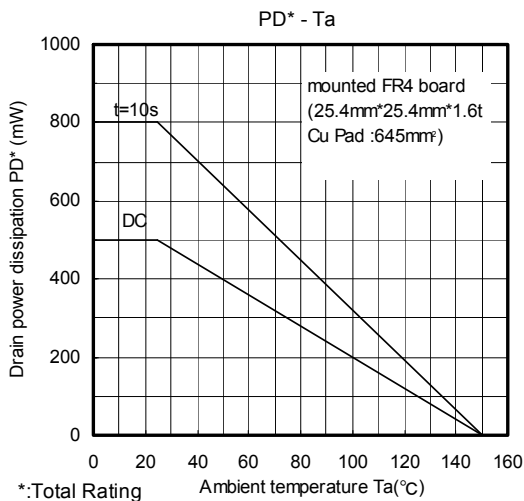
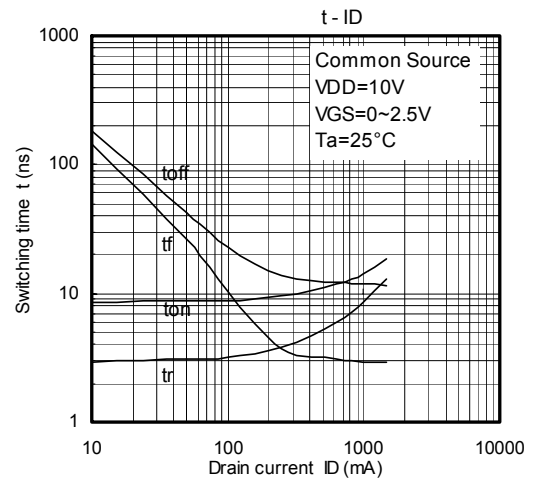
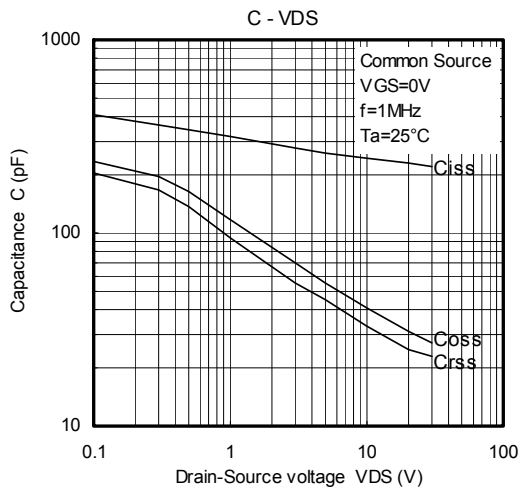
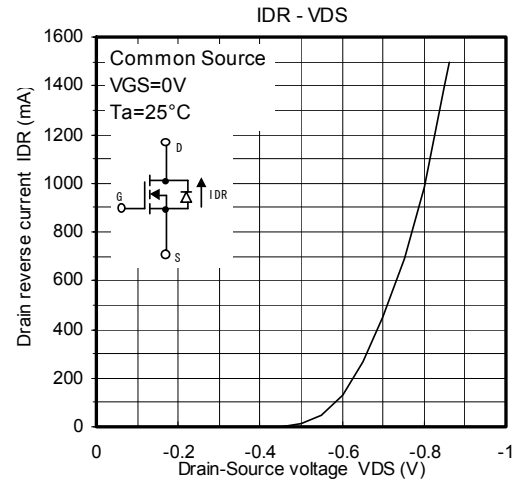
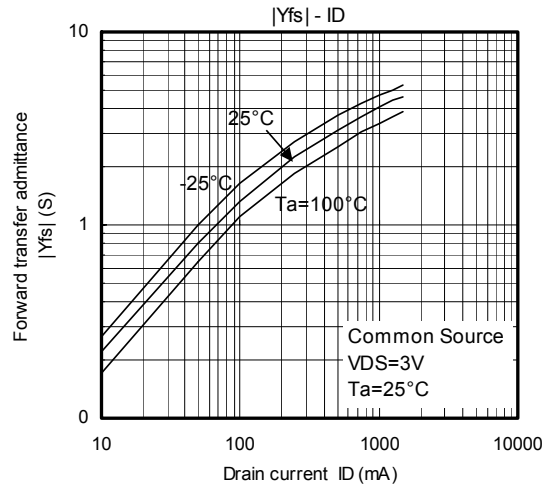
Precaution

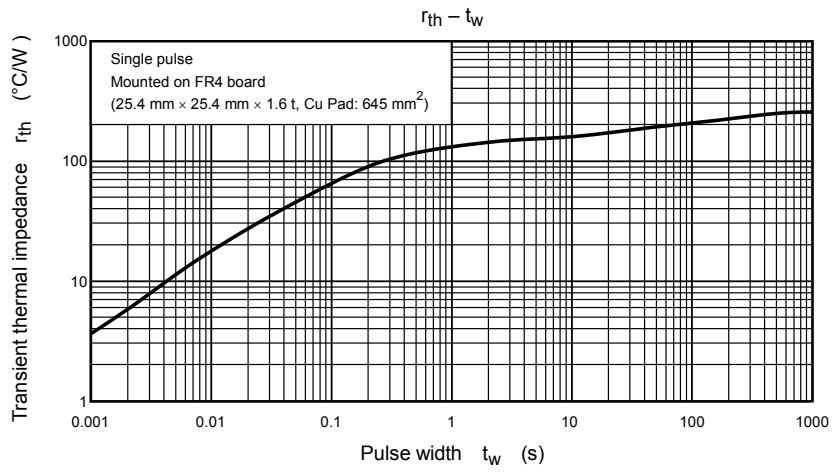
V_{th} can be expressed as the voltage between gate and source when the low operating current value is $I_D = 100\text{ }\mu\text{A}$ for this product. For normal switching operation, $V_{GS(ON)}$ requires a higher voltage than V_{th} and $V_{GS(OFF)}$ requires a lower voltage than V_{th} .

(The relationship can be established as follows: $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$)

Please take this into consideration when using the device. The V_{GS} recommended voltage for turning on this product is 2.5 V or higher.







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